

## Monolithic Dual SPST CMOS Analog Switch

### FEATURES

- $\pm 15\text{ V}$  Input Signal Range
- 44-V Maximum Supply Ranges
- On-Resistance:  $45\ \Omega$
- TTL and CMOS Compatibility

### BENEFITS

- Wide Dynamic Range
- Simple Interfacing
- Reduced External Component Count

### APPLICATIONS

- Servo Control Switching
- Programmable Gain Amplifiers
- Audio Switching
- Programmable Filters

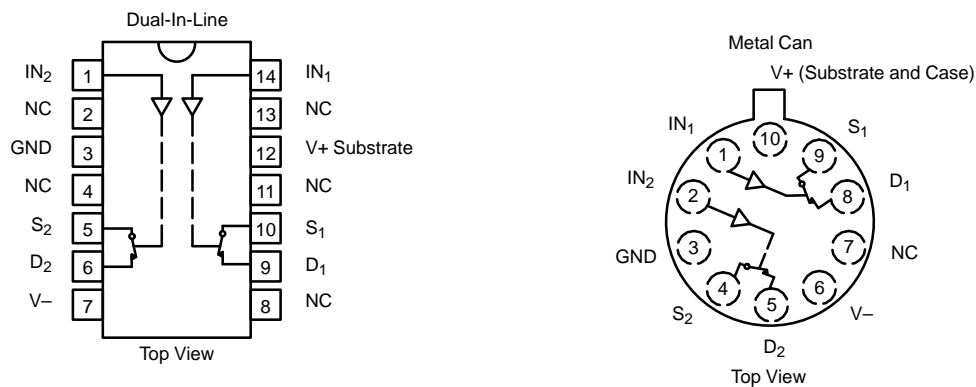
### DESCRIPTION

The DG200A is a dual, single-pole, single-throw analog switch designed to provide general purpose switching of analog signals. This device is ideally suited for designs requiring a wide analog voltage range coupled with low on-resistance.

Each switch conducts equally well in both directions when on, and blocks up to 30 V peak-to-peak when off. In the on condition, this bi-directional switch introduces no offset voltage of its own.

The DG200A is designed on Vishay Siliconix' improved PLUS-40 CMOS process. An epitaxial layer prevents latchup.

### FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



### TRUTH TABLE

Logic	Switch
0	ON
1	OFF

Logic "0"  $\leq 0.8\text{ V}$   
Logic "1"  $\geq 2.4\text{ V}$

ORDERING INFORMATION		
Temp Range	Package	Part Number
0 to 70°C	14-Pin Plastic DIP	DG200ACJ
-25 to 85°C	14-Pin CerDIP	DG200ABK
	10-Pin Metal Can	DG200ABA
-55 to 125°C	14-Pin CerDIP	DG200AAK
		DG200AAK/883, JM38510/12301BCA, 5962-9562901QCA
	10-Pin Metal Can	DG200AAA
		DG200AAA/883, JM38510/12301BIC
14-Pin Sidebrazed	JM38510/12301BCC	

**ABSOLUTE MAXIMUM RATINGS**

V+ to V-	44 V
GND to V-	25 V
Digital Inputs <sup>a</sup> , V <sub>S</sub> , V <sub>D</sub>	(V-) -2 V to (V+) +2 V or 30 mA, whichever occurs first
Current (Any Terminal) Continuous	30 mA
Current S or D (Pulsed at 1 ms, 10% Duty Cycle Max)	100 mA
Storage Temperature (AX, BX Suffix)	-65 to 150°C
(CJ Suffix)	-65 to 125°C

Power Dissipation (Package) <sup>b</sup>	
10-Pin Metal Can <sup>c</sup>	450 mW
14-Pin CerDIP <sup>d</sup>	825 mW
14-Pin Plastic DIP <sup>e</sup>	470 mW

- Notes:
- Signals on S<sub>X</sub>, D<sub>X</sub>, or I<sub>NX</sub> exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
  - All leads welded or soldered to PC Board.
  - Derate 6 mW/°C above 75°C
  - Derate 11 mW/°C above 75°C
  - Derate 6.5 mW/°C above 25°C

**SCHEMATIC DIAGRAM (TYPICAL CHANNEL)**

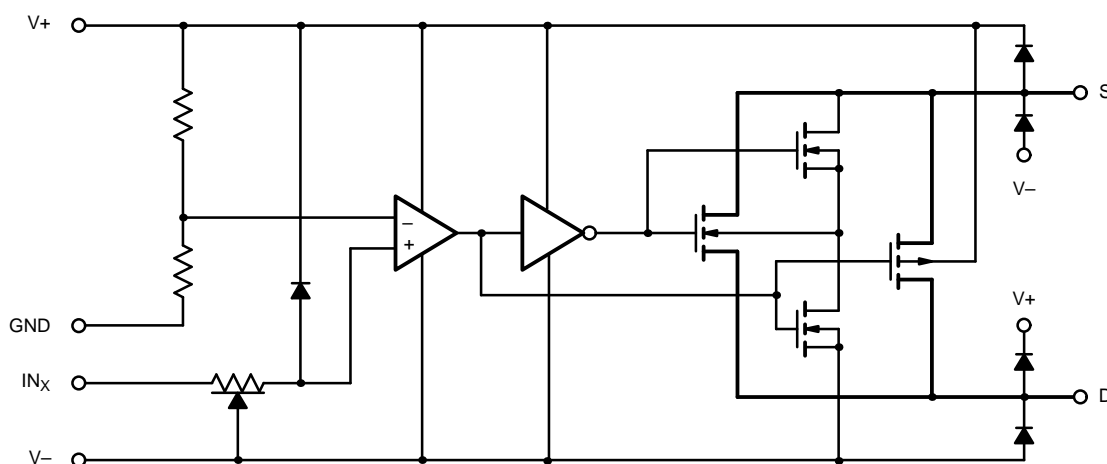


FIGURE 1.

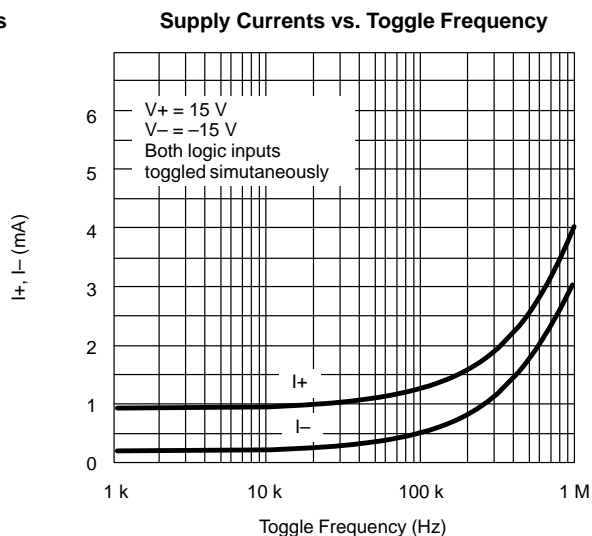
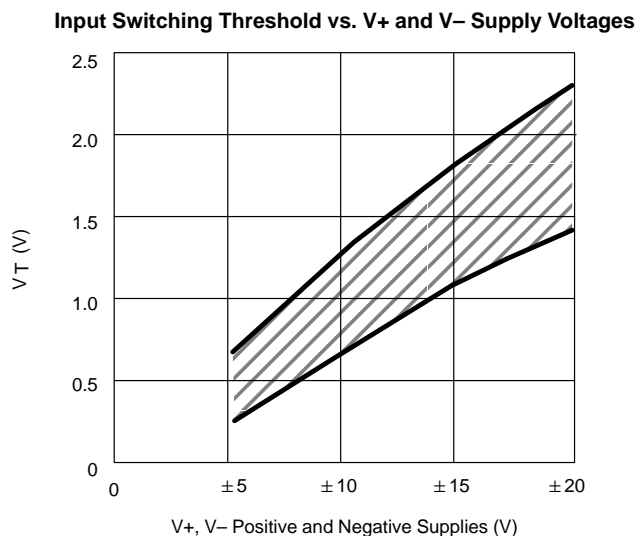
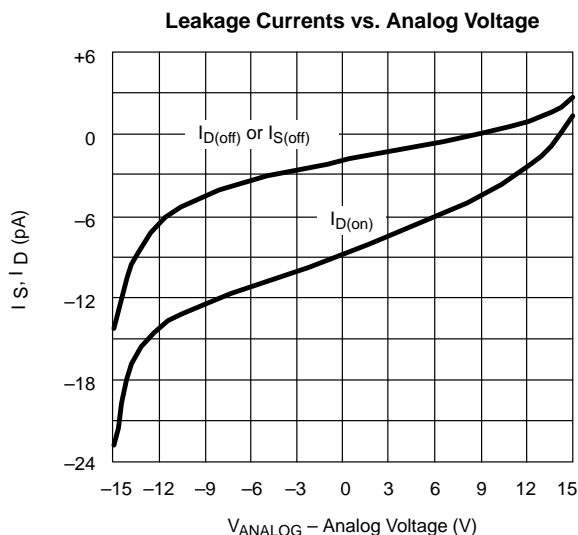
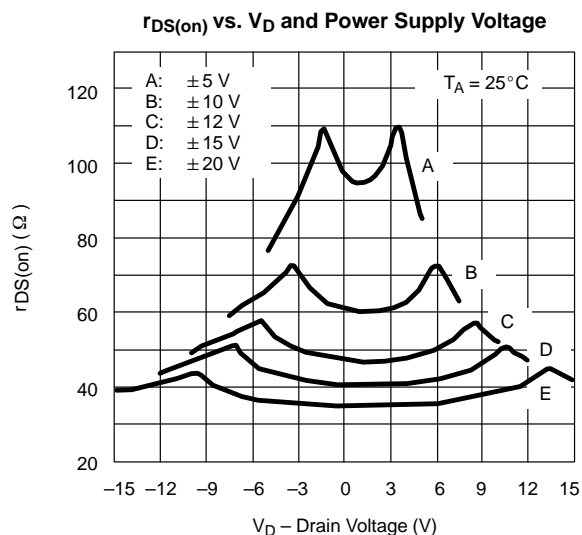


SPECIFICATIONS <sup>a</sup>									
Parameter	Symbol	Test Conditions Unless Otherwise Specified $V_+ = 15\text{ V}$ , $V_- = -15\text{ V}$ $V_{IN} = 2.4\text{ V}$ , $0.8\text{ V}^f$	Temp <sup>b</sup>	Typ <sup>c</sup>	A Suffix -55 to 125°C		B, C Suffix		Unit
					Min <sup>d</sup>	Max <sup>d</sup>	Min <sup>d</sup>	Max <sup>d</sup>	
<b>Analog Switch</b>									
Analog Signal Range <sup>e</sup>	$V_{ANALOG}$		Full		-15	15	-15	15	V
Drain-Source On-Resistance	$r_{DS(on)}$	$V_D = \pm 10\text{ V}$ , $I_S = -1\text{ mA}$	Room Full	45		70 100		80 100	$\Omega$
Source Off Leakage Current	$I_{S(off)}$	$V_S = \pm 14\text{ V}$ , $V_D = \mp 14\text{ V}$	Room Full	$\pm 0.01$	-2 -100	2 100	-5 -100	5 100	nA
Drain Off Leakage Current	$I_{D(off)}$	$V_D = \pm 14\text{ V}$ , $V_S = \mp 14\text{ V}$	Room Full	$\pm 0.01$	-2 -100	2 100	-5 -100	5 100	
Channel On Leakage Current <sup>f</sup>	$I_{D(on)}$	$V_S = V_D = \pm 14\text{ V}$	Room Full	$\pm 0.1$	-2 -200	2 200	-5 -200	5 200	
<b>Digital Control</b>									
Input Current with Input Voltage High	$I_{INH}$	$V_{IN} = 2.4\text{ V}$	Room Full	0.0009	-0.5 -1		-1 -10		$\mu\text{A}$
		$V_{IN} = 15\text{ V}$	Room Full	0.005		0.5 1		1 10	
Input Current with Input Voltage Low	$I_{INL}$	$V_{IN} = 0\text{ V}$	Room Full	-0.0015	-0.5 -1		-1 -10		
<b>Dynamic Characteristics</b>									
Turn-On Time	$t_{ON}$	See Switching Time Test Circuit	Room	440		1000		1000	ns
Turn-Off Time	$t_{OFF}$		Room	340		425		425	
Charge Injection	Q	$C_L = 1000\text{ pF}$ , $V_g = 0\text{ V}$ $R_g = 0\ \Omega$	Room	-10					pC
Source-Off Capacitance	$C_{S(off)}$	$f = 140\text{ kHz}$ $V_{IN} = 5\text{ V}$	Room	9					pF
Drain-Off Capacitance	$C_{D(off)}$		$V_S = 0\text{ V}$ $V_D = 0\text{ V}$	Room	9				
Channel-On Capacitance	$C_{D(on)} + C_{S(on)}$	$V_D = V_S = 0\text{ V}$ , $V_{IN} = 0\text{ V}$	Room	25					
Off Isolation	OIRR	$V_{IN} = 5\text{ V}$ , $R_L = 75\ \Omega$ $V_S = 2\text{ V}$ , $f = 1\text{ MHz}$	Room	75					dB
Crosstalk (Channel-to-Channel)	$X_{TALK}$		Room	90					
<b>Power Supplies</b>									
Positive Supply Current	I+	Both Channels On or Off $V_{IN} = 0\text{ V}$ and $2.4\text{ V}$	Room	0.8		2		2	mA
Negative Supply Current	I-		Room	-0.23	-1		-1		

Notes:

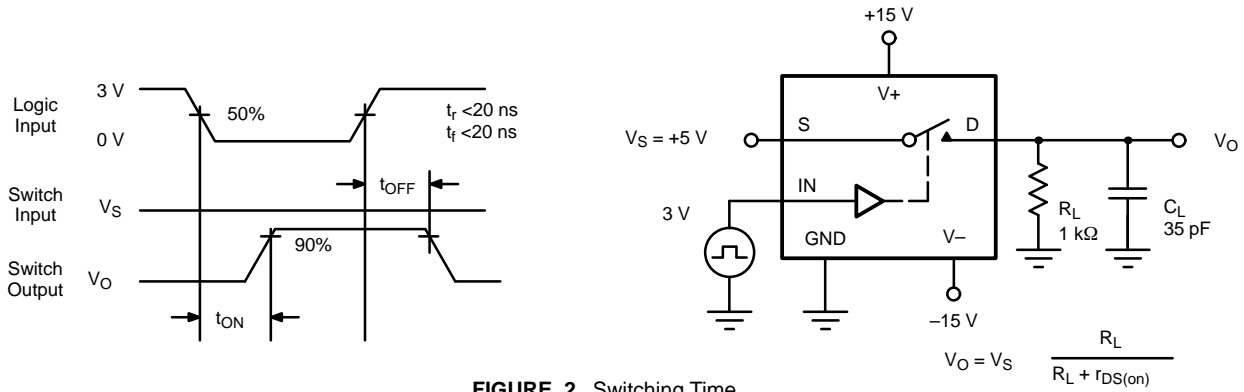
- Refer to PROCESS OPTION FLOWCHART.
- Room = 25°C, Full = as determined by the operating temperature suffix.
- Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
- The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- Guaranteed by design, not subject to production test.
- $V_{IN}$  = input voltage to perform proper function.

**TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)**

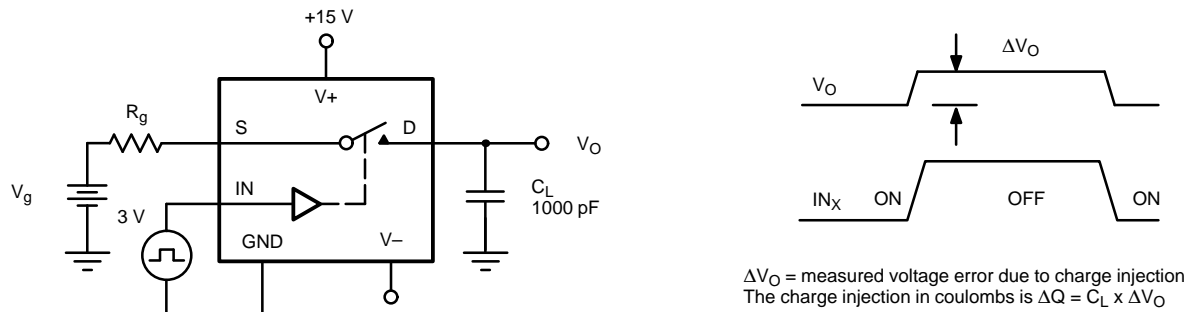


**TEST CIRCUITS**

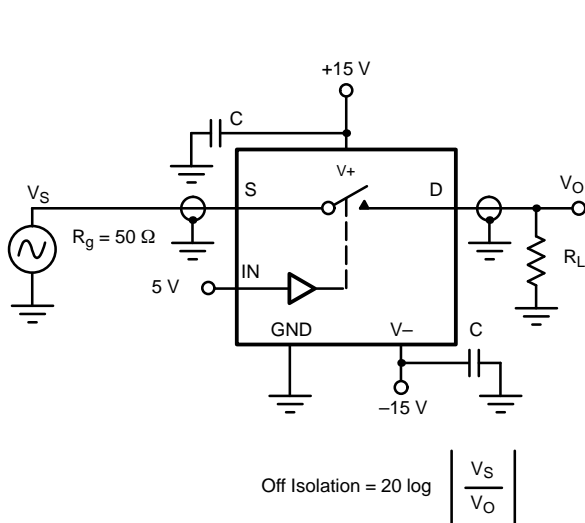
$V_O$  is the steady state output with switch on. Feedthrough via gate capacitance may result in spikes at leading and trailing edge of output waveform.



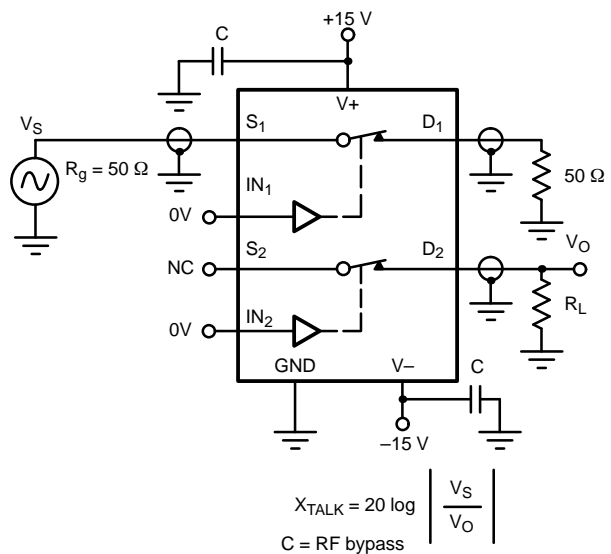
**FIGURE 2. Switching Time**



**FIGURE 3. Charge Injection**



**FIGURE 4. Off Isolation**



**FIGURE 5. Channel-to-Channel Crosstalk**